ALPHA & OMEGA SEMICONDUCTOR

AOL1420
N-Channel Enhancement Mode Field Effect Transistor

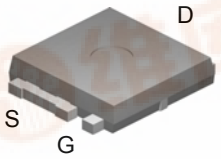
General Description

The AOL1420 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and low gate resistance. This device is ideally suited for use as a low side switch in CPU core power conversion. *Standard Product AOL1420 is Pb-free (meets ROHS & Sony 259 specifications). AOL1420L is a Green Product ordering option. AOL1420 and AOL1420L are electrically identical.*

Features

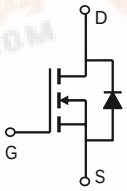
V_{DS} (V) = 30V
I_D = 85A (V_{GS} = 10V)
$R_{DS(ON)}$ < 3.7mΩ (V_{GS} = 10V)
$R_{DS(ON)}$ < 5.5mΩ (V_{GS} = 4.5V)

Ultra SO-8™ Top View



Bottom tab connected to drain

Fits SOIC8 footprint !



Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current [B,G]	T_C=25°C [G]	I_D	85	A
	T_C=100°C [B]		63	
Pulsed Drain Current		I_{DM}	150	
Continuous Drain Current [G]	T_A=25°C	I_{DSM}	18	
	T_A=70°C		14	
Avalanche Current [C]		I_{AR}	30	A
Repetitive avalanche energy L=0.1mH [C]		E_{AR}	112	mJ
Power Dissipation [B]	T_C=25°C	P_D	100	W
	T_C=100°C		50	
Power Dissipation [A]	T_A=25°C	P_{DSM}	2.1	W
	T_A=70°C		1.3	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 175	°C

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	19.6	25	°C/W
Maximum Junction-to-Ambient [A]	Steady-State		50	60	°C/W
Maximum Junction-to-Case [C]	Steady-State	$R_{\theta JC}$	0.9	1.5	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250µA, V_{GS}=0V	30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=24V, V_{GS}=0V			1	µA
		T_J=55°C			5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}= ±20V			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} I_D=250µA	1	1.8	3	V
$I_{D(ON)}$	On state drain current	V_{GS}=10V, V_{DS}=5V	85			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=20A		2.9	3.7	mΩ
		T_J=125°C		4.4	5.5	
		V_{GS}=4.5V, I_D=20A		4.4	5.5	mΩ
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=20A		106		S
V_{SD}	Diode Forward Voltage	I_S=1A,V_{GS}=0V		0.72	1	V
I_S	Maximum Body-Diode Continuous Current				85	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=15V, f=1MHz		3200	3840	pF
C_{oss}	Output Capacitance			590		pF
C_{rss}	Reverse Transfer Capacitance			414		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz		0.54	0.7	Ω
SWITCHING PARAMETERS						
Q_g(10V)	Total Gate Charge	V_{GS}=4.5V, V_{DS}=15V, I_D=20A		63	76	nC
Q_g(4.5V)	Total Gate Charge			33	40	nC
Q_{gs}	Gate Source Charge			8.6		nC
Q_{gd}	Gate Drain Charge			17.6		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=15V, R_L=0.75Ω, R_{GEN}=3Ω		12		ns
t_r	Turn-On Rise Time			15.5		ns
$t_{D(off)}$	Turn-Off DelayTime			40		ns
t_f	Turn-Off Fall Time			14		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=20A, dI/dt=100A/µs		34	41	ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=20A, dI/dt=100A/µs		30		nC

A: The value of R qJA is measured with the device in a still air environment with T A =25°C.
B. The power dissipation PD is based on TJ(MAX)=175°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
C: Repetitive rating, pulse width limited by junction temperature TJ(MAX)=175°C.
D. The R qJA is the sum of the thermal impedence from junction to case R qJC and case to ambient.
E. The static characteristics in Figures 1 to 6 are obtained using <300 ms pulses, duty cycle 0.5% max.
F. These curves are based on the junction-to-case thermal impedence which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of TJ(MAX)=175°C.
G. The maximum current rating is limited by bond-wires.
Rev0: August 2005

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

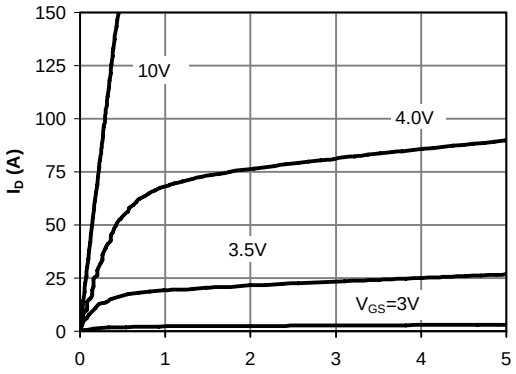


Fig 1: On-Region Characteristics

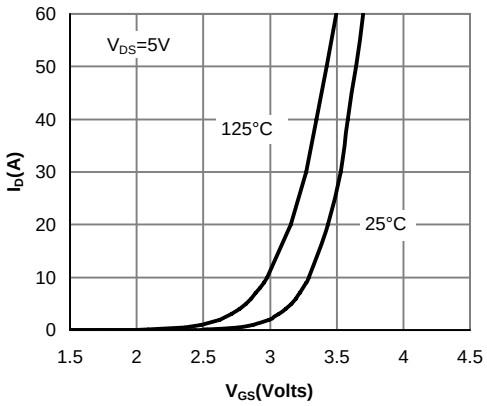


Figure 2: Transfer Characteristics

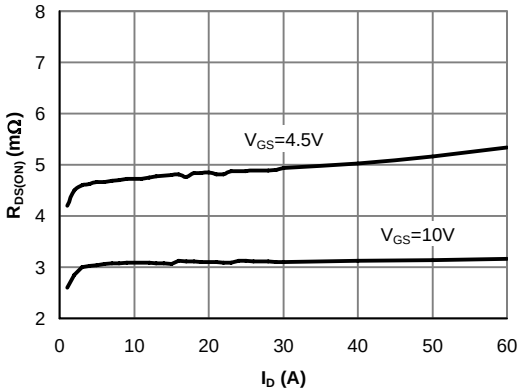


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

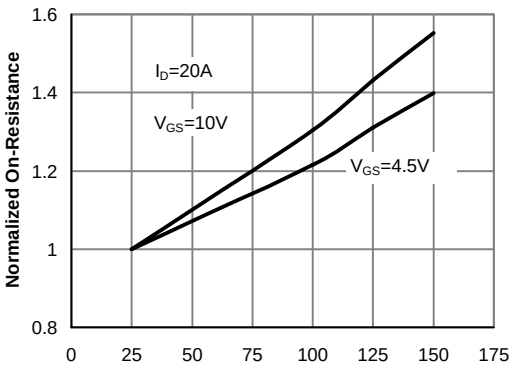


Figure 4: On-Resistance vs. Junction Temperature

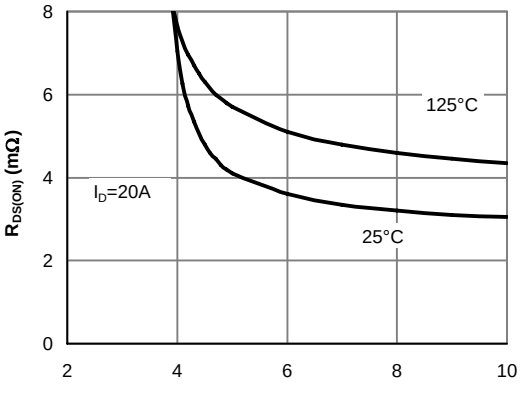


Figure 5: On-Resistance vs. Gate-Source Voltage

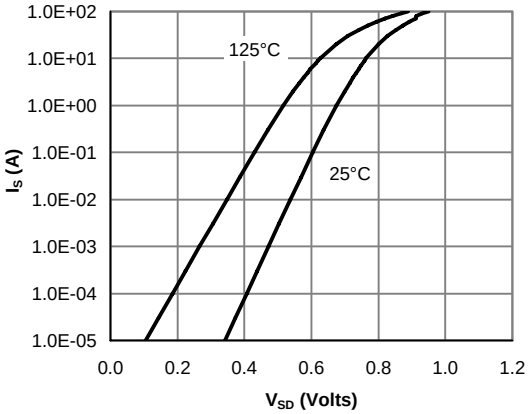


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

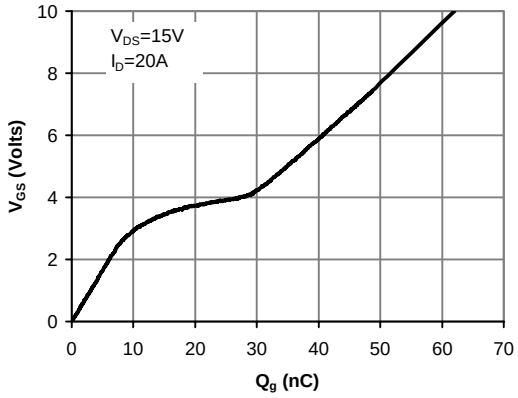


Figure 7: Gate-Charge Characteristics

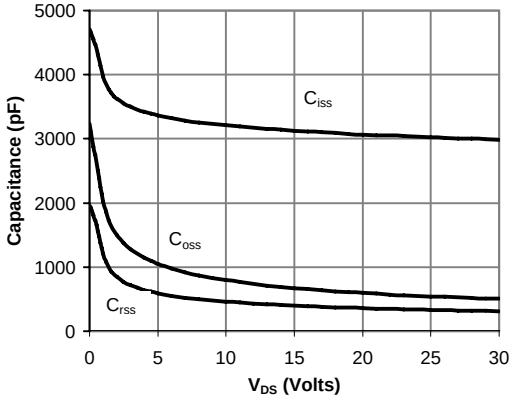


Figure 8: Capacitance Characteristics

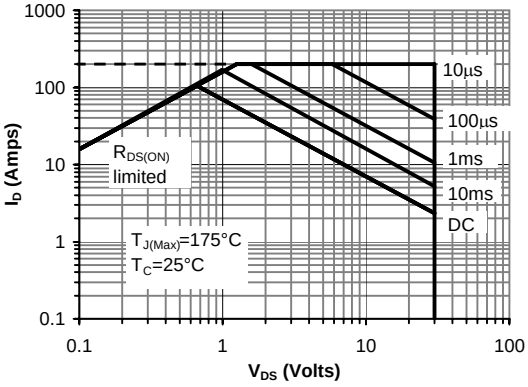


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

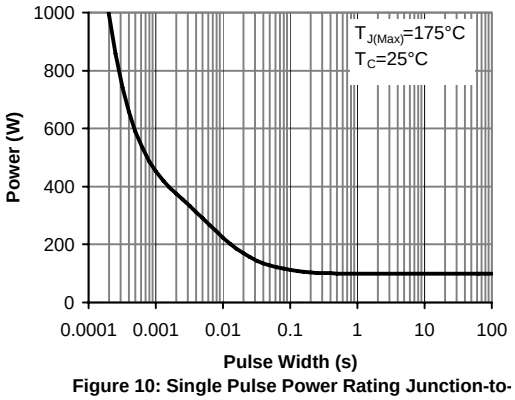


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

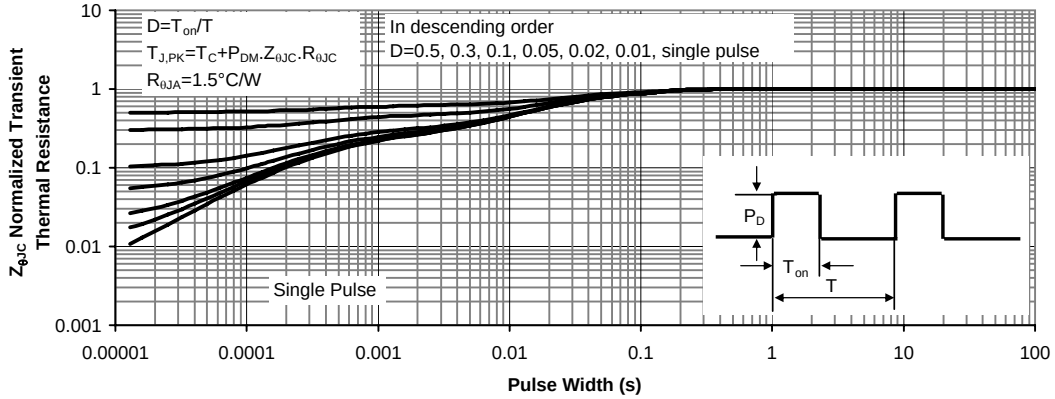


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

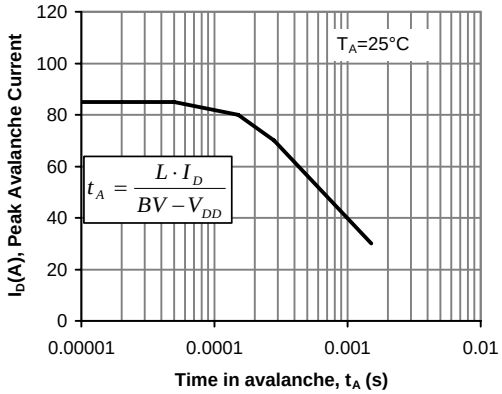


Figure 12: Single Pulse Avalanche capability

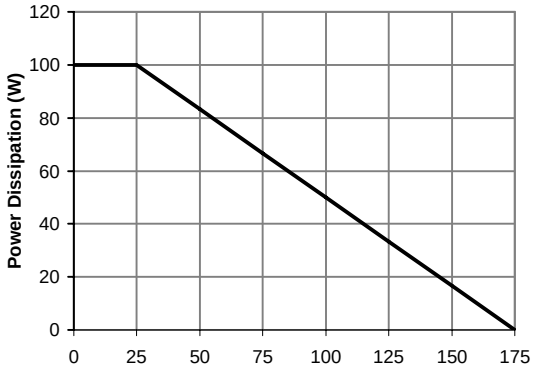


Figure 13: Power De-rating (Note B)

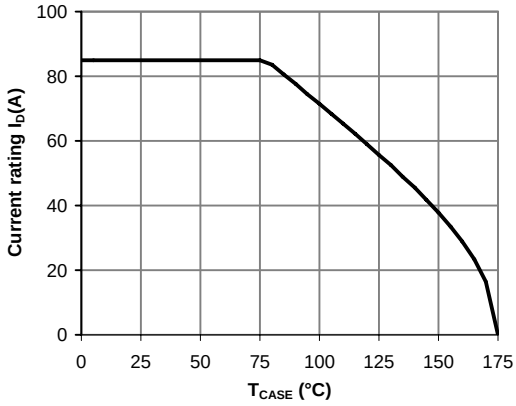


Figure 14: Current De-rating (Note B)

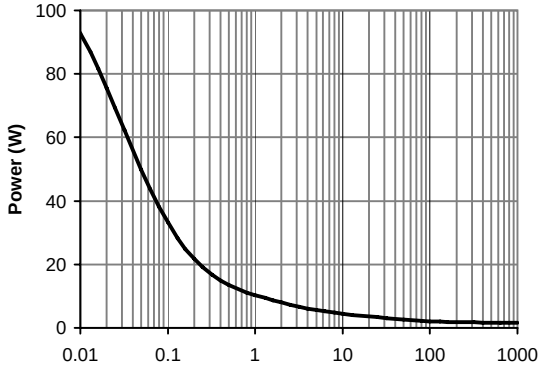


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note H)

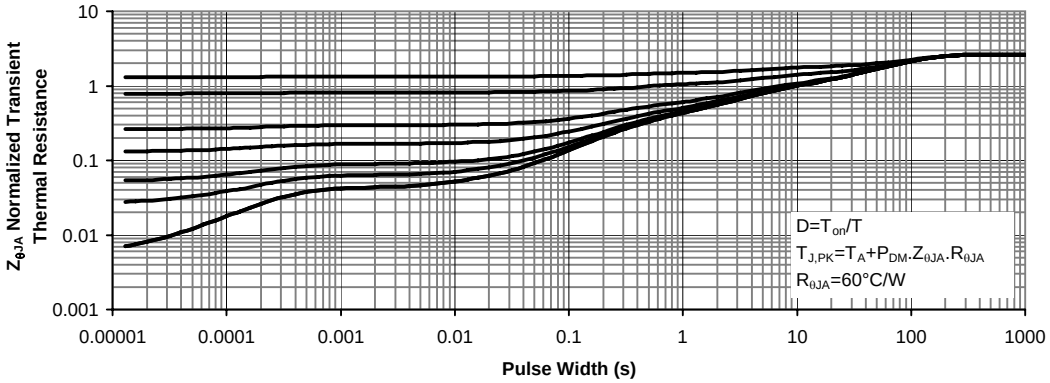


Figure 16: Normalized Maximum Transient Thermal Impedance (Note H)